

PATTERN DEFINITION OF MRAM DEVICE USING CHEMICAL

MECHANICAL POLISHING

This application is a con of 10/119,952 4/11/2002
FIELD OF INVENTION PAT 6,673,675.

[0001] The present invention relates to a magnetic random access memory (MRAM) and a fabricating method thereof, and more particularly to a method of forming the MRAM cells.

BACKGROUND OF THE INVENTION

[0002] Magnetic random access memories (MRAMs) employ memory cells having magnetic multilayer films as storage elements. When in use, an MRAM cell stores information as digital bits, in the form of relative magnetic orientations of spaced thin magnetic multilayer films forming each memory cell. Each MRAM cell has two stable magnetic film orientations, one which produces a high resistance across the cell representing e.g. a logic state 0 and another which produces a lower resistance across the cell representing e.g. a logic state 1, or vice versa.

[0003] A typical multilayer-film MRAM array includes a number of bit or digit (column) lines intersected by a number of word (row) lines. An MRAM cell is formed between a digit and row line at each intersection.

AMENDMENTS TO THE SPECIFICATION

Please amend the Title as follows:

**METHODS OF FABRICATING AN MRAM DEVICE FABRICATED USING
CHEMICAL MECHANICAL POLISHING**

AMENDMENTS TO THE SPECIFICATION

Please amend the title as follows:

Delete "PATTERN DEFINITION OF MRAM DEVICE USING CHEMICAL MECHANICAL POLISHING " and insert - METHODS OF FABRICATING AN MRAM DEVICE USING CHEMICAL MECHANICAL POLISHING -- in its place.

Immediately after the heading "FIELD OF INVENTION" on page 1 of the specification, add the following:

--This application is a continuation of U.S. Patent Application 10/119,952, filed on
now Patent No. 6,673,675
April 11, 2002 *(allowed)*. --